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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	27
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K × 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l052k8t6d

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 93.	Document revision history	······································	138
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3.8 Memories

The STM32L052x6/8 devices have the following features:

- 8 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
 - 32 or 64 Kbytes of embedded Flash program memory
 - 2 Kbytes of data EEPROM
 - Information block containing 32 user and factory options bytes plus 4 Kbytes of system memory

The user options bytes are used to write-protect or read-out protect the memory (with 4 Kbyte granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no protection
- Level 1: memory readout protected.

The Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected

• Level 2: chip readout protected, debug features (Cortex-M0+ serial wire) and boot in RAM selection disabled (debugline fuse)

The firewall protects parts of code/data from access by the rest of the code that is executed outside of the protected area. The granularity of the protected code segment or the non-volatile data segment is 256 bytes (Flash memory or EEPROM) against 64 bytes for the volatile data segment (RAM).

The whole non-volatile memory embeds the error correction code (ECC) feature.

3.9 Boot modes

At startup, BOOT0 pin and nBOOT1 option bit are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using SPI1(PA4, PA5, PA6, PA7) or SPI2 (PB12, PB13, PB14, PB15), USART1(PA9, PA10) or USART2(PA2, PA3). See STM32[™] microcontroller system memory boot mode AN2606 for details.



3.10 Direct memory access (DMA)

The flexible 7-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I²C, USART, LPUART, general-purpose timers, DAC, and ADC.

3.11 Analog-to-digital converter (ADC)

A native 12-bit, extended to 16-bit through hardware oversampling, analog-to-digital converter is embedded into STM32L052x6/8 device. It has up to 16 external channels and 3 internal channels (temperature sensor, voltage reference). Three channels, PA0, PA4 and PA5, are fast channels, while the others are standard channels.

The ADC performs conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC frequency is independent from the CPU frequency, allowing maximum sampling rate of 1.14 MSPS even with a low CPU speed. The ADC consumption is low at all frequencies (~25 μ A at 10 kSPS, ~200 μ A at 1MSPS). An auto-shutdown function guarantees that the ADC is powered off except during the active conversion phase.

The ADC can be served by the DMA controller. It can operate from a supply voltage down to 1.65 V.

The ADC features a hardware oversampler up to 256 samples, this improves the resolution to 16 bits (see AN2668).

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions and timers.

3.12 Temperature sensor

The temperature sensor (T_{SENSE}) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC_IN18 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.



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3.14 Ultra-low-power comparators and reference voltage

The STM32L052x6/8 embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with ultra low consumption
- One comparator with rail-to-rail inputs, fast or slow mode.
- The threshold can be one of the following:
 - DAC output
 - External I/O pins
 - Internal reference voltage (V_{REFINT})
 - submultiple of Internal reference voltage(1/4, 1/2, 3/4) for the rail to rail comparator.

Both comparators can wake up the devices from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 μ A typical).

3.15 System configuration controller

The system configuration controller provides the capability to remap some alternate functions on different I/O ports.

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM21, TIM22 and LPTIM timer input captures. It also controls the routing of internal analog signals to the USB internal oscillator, ADC, COMP1 and COMP2 and the internal reference voltage V_{REFINT} .

3.16 Touch sensing controller (TSC)

The STM32L052x6/8 provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 24 capacitive sensing channels distributed over 8 analog I/O groups.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (such as glass, plastic). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. To limit the CPU bandwidth usage, this acquisition is directly managed by the hardware touch sensing controller and only requires few external components to operate.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library, which is free to use and allows touch sensing functionality to be implemented reliably in the end application.



3.17.1 General-purpose timers (TIM2, TIM21 and TIM22)

There are three synchronizable general-purpose timers embedded in the STM32L052x6/8 devices (see *Table 10* for differences).

TIM2

TIM2 is based on 16-bit auto-reload up/down counter. It includes a 16-bit prescaler. It features four independent channels each for input capture/output compare, PWM or one-pulse mode output.

The TIM2 general-purpose timers can work together or with the TIM21 and TIM22 generalpurpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2 has independent DMA request generation.

This timer is capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

TIM21 and TIM22

TIM21 and TIM22 are based on a 16-bit auto-reload up/down counter. They include a 16-bit prescaler. They have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can work together and be synchronized with the TIM2, full-featured general-purpose timers.

They can also be used as simple time bases and be clocked by the LSE clock source (32.768 kHz) to provide time bases independent from the main CPU clock.

3.17.2 Low-power Timer (LPTIM)

The low-power timer has an independent clock and is running also in Stop mode if it is clocked by LSE, LSI or an external clock. It is able to wakeup the devices from Stop mode.

This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous / one shot mode
- Selectable software / hardware input trigger
- Selectable clock source
 - Internal clock source: LSE, LSI, HSI or APB clock
 - External clock source over LPTIM input (working even with no internal clock source running, used by the Pulse Counter Application)
- Programmable digital glitch filter
- Encoder mode

3.17.3 Basic timer (TIM6)

This timer can be used as a generic 16-bit timebase. It is mainly used for DAC trigger generation.



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		Pin Nu	ımber								
LQFP32	UFQFN32	WLCSP36 ⁽¹⁾	LQFP48	LQFP64	TFBGA64	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	-	-	54	B5	PD2	I/O	FT	-	LPUART1_RTS_DE	-
26	26	В3	39	55	A5	PB3	I/O	FT	-	SPI1_SCK, TIM2_CH2, TSC_G5I_O1, EVENTOUT	COMP2_INN
27	27	A3	40	56	A4	PB4	I/O	FT	-	SPI1_MISO, EVENTOUT, TSC_G5_IO2, TIM22_CH1	COMP2_INP
28	28	C4	41	57	C4	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM22_CH2	COMP2_INP
29	29	B4	42	58	D3	PB6	I/O	FTf	-	USART1_TX, I2C1_SCL, LPTIM1_ETR, TSC_G5_IO3	COMP2_INP
30	30	A4	43	59	C3	PB7	I/O	FTf	-	USART1_RX, I2C1_SDA, LPTIM1_IN2, TSC_G5_IO4	COMP2_INP, PVD_IN
31	31	C5	44	60	B4	BOOT0	В	-	-	-	-
-	32	B5	45	61	B3	PB8	I/O	FTf	-	TSC_SYNC, I2C1_SCL	-
-	-	-	46	62	A3	PB9	I/O	FTf	-	EVENTOUT, I2C1_SDA, SPI2_NSS/I2S2_WS	-
32	-	D6	47	63	D4	VSS	S	-	-	-	-
1	1	A5	48	64	E4	VDD	S	-	-	-	-

Table 16. STM32L052x6/8 pin definitions (continued)

1. PB9/12/13/14/15, PH0/1 and PC13 GPIOs should be configured as output and driven Low, even if they are not available on this package.

2. PA4 offers a reduced touch sensing sensitivity. It is thus recommended to use it as sampling capacitor I/O.

3. These pins are powered by VDD_USB. For all characteristics that refer to V_{DD} , V_{DD_USB} must be used instead.



		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Po	ort	SPI1/TIM21/SYS_A F/EVENTOUT/	-	USB/TIM2/ EVENTOUT/	TSC/ EVENTOUT	USART1/2/3	TIM2/21/22	EVENTOUT	COMP1/2
	PA0	-	-	TIM2_CH1	TSC_G1_IO1	USART2_CTS	TIM2_ETR	-	COMP1_OUT
	PA1	EVENTOUT	-	TIM2_CH2	TSC_G1_IO2	USART2_RTS_ DE	TIM21_ETR	-	-
	PA2	TIM21_CH1	-	TIM2_CH3	TSC_G1_IO3	USART2_TX	-	-	COMP2_OU
	PA3	TIM21_CH2	-	TIM2_CH4	TSC_G1_IO4	USART2_RX	-	-	-
	PA4	SPI1_NSS	-	-	TSC_G2_IO1	USART2_CK	TIM22_ETR	-	-
	PA5	SPI1_SCK	-	TIM2_ETR	TSC_G2_IO2		TIM2_CH1	-	-
	PA6	SPI1_MISO	-	-	TSC_G2_IO3	LPUART1_CTS	TIM22_CH1	EVENTOUT	COMP1_OU
Port A	PA7	SPI1_MOSI	-	-	TSC_G2_IO4		TIM22_CH2	EVENTOUT	COMP2_OU
Port A	PA8	МСО	-	USB_CRS_SYNC	EVENTOUT	USART1_CK	-	-	-
	PA9	МСО	-	-	TSC_G4_IO1	USART1_TX	-	-	-
	PA10	-	-	-	TSC_G4_IO2	USART1_RX	-	-	-
	PA11	SPI1_MISO	-	EVENTOUT	TSC_G4_IO3	USART1_CTS	-	-	COMP1_OU
	PA12	SPI1_MOSI	-	EVENTOUT	TSC_G4_IO4	USART1_RTS_ DE	-	-	COMP2_OU
	PA13	SWDIO	-	USB_NOE	-	-	-	-	-
	PA14	SWCLK	-	-	-	USART2_TX	-	-	-
	PA15	SPI1_NSS	-	TIM2_ETR	EVENTOUT	USART2_RX	TIM2_CH1	-	-

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Pin descriptions

STM32L052x6 STM32L052x8

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 22: Voltage characteristics*, *Table 23: Current characteristics*, and *Table 24: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard. Extended mission profiles are available on demand.

Symbol	Definition	Min	Мах	Unit
V _{DD} -V _{SS}	External main supply voltage (including V _{DDA} , V _{DD_USB} , V _{DD}) ⁽¹⁾	-0.3	4.0	
	Input voltage on FT and FTf pins	V _{SS} –0.3	V _{DD} +4.0	
V _{IN} ⁽²⁾	Input voltage on TC pins	V _{SS} –0.3	4.0	V
VIN Y	Input voltage on BOOT0	V _{SS}	V _{DD} +4.0	
	Input voltage on any other pin	V _{SS} -0.3	4.0	
$ \Delta V_{DD} $	Variations between different V_{DDx} power pins	-	50	
V _{DDA} -V _{DDx}	Variations between any V_{DDx} and V_{DDA} power $\mbox{pins}^{(3)}$	-	300	mV
$ \Delta V_{SS} $	Variations between all different ground pins	-	50	
V _{REF+} –V _{DDA}	Allowed voltage difference for $V_{REF^+} > V_{DDA}$	-	0.4	V
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Sect	ion 6.3.11	

1. All main power (V_{DD},V_{DD} USB, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. V_{IN} maximum must always be respected. Refer to *Table* 23 for maximum allowed injected current values.

3. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and device operation. V_{DD_USB} is independent from V_{DD} and V_{DDA}: its value does not need to respect this rule.



Symbol	Parameter	Conditions	Min	Max	Unit
		Maximum power dissipation (range 6)	-40	85	
TA	Temperature range	emperature range Maximum power dissipation (range 7)		105	
		Maximum power dissipation (range 3)	-40	125	°C
	Junction temperature range (range 6)	-40 °C ≤T _A ≤85 °	-40	105	
TJ J	Junction temperature range (range 7)	-40 °C ≤T _A ≤105 °C	-40	125	
	Junction temperature range (range 3)	-40 °C ≤T _A ≤125 °C	-40	130	

Table 25. General operating conditions (continued)

1. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and normal operation.

2. V_{DD_USB} must respect the following conditions:

- When V_{DD} is powered-on (V_{DD} < V_{DD_min}), V_{DD_USB} should be always lower than V_{DD.}

- When V_{DD} is powered-down (V_{DD} < V_{DD_min}), V_{DD_USB} should be always lower than V_{DD}.

- In operating mode, V_{DD_USB} could be lower or higher $V_{DD.}$

- If the USB is not used, V_{DD_USB} must range from V_{DD_min} to V_{DD_max} to be able to use PA11 and PA12 as standard I/Os.

3. To sustain a voltage higher than V_{DD} +0.3V, the internal pull-up/pull-down resistors must be disabled.

If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see Table 24: Thermal characteristics on page 56).



		0		/		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{LPBUF} ⁽⁴⁾	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V _{REFINT_DIV1} ⁽⁴⁾	1/4 reference voltage	-	24	25	26	
V _{REFINT_DIV2} ⁽⁴⁾	1/2 reference voltage	-	49	50	51	% V _{REFINT}
V _{REFINT_DIV3} ⁽⁴⁾	3/4 reference voltage	-	74	75	76	

Table 28. Embedded internal reference voltage⁽¹⁾ (continued)

1. Refer to *Table 40: Peripheral current consumption in Stop and Standby mode* for the value of the internal reference current consumption (I_{REFINT}).

2. Guaranteed by test in production.

3. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.

4. Guaranteed by design.

5. Shortest sampling time can be determined in the application by multiple iterations.

6. To guarantee less than 1% VREF_OUT deviation.

6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in *Figure 13: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code if not specified otherwise.

The current consumption values are derived from the tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 25: General operating conditions* unless otherwise specified.

The MCU is placed under the following conditions:

- All I/O pins are configured in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time and prefetch is adjusted depending on fHCLK frequency and voltage range to provide the best CPU performance unless otherwise specified.
- When the peripherals are enabled f_{APB1} = f_{APB2} = f_{APB}
- When PLL is ON, the PLL inputs are equal to HSI = 16 MHz (if internal clock is used) or HSE = 16 MHz (if HSE bypass mode is used)
- The HSE user clock applied to OSCI_IN input follows the characteristic specified in *Table 42: High-speed external user clock characteristics*
- For maximum current consumption $V_{DD} = V_{DDA} = 3.6$ V is applied to all supply pins
- For typical current consumption $V_{DD} = V_{DDA} = 3.0$ V is applied to all supply pins if not specified otherwise

The parameters given in *Table 50*, *Table 25* and *Table 26* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 25*.



2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Symbol	Parameter		Тур	Max ⁽¹⁾	Unit		
				$T_A = -40 \text{ to } 25^{\circ}\text{C}$	8.5	10	
			MSI clock = 65 kHz,	T _A = 85 °C	11.5	48	
			f _{HCLK} = 32 kHz	T _A = 105 °C	15.5	53	
				T _A = 125 °C	27.5	130	
	All peripherals		$T_A = -40 \text{ °C to } 25 \text{ °C}$	10	15		
		OFF, code executed from	MSI clock= 65 kHz,	T _A = 85 °C	15.5	50	
	RAM, Flash	f _{HCLK} = 65 kHz	T _A = 105 °C	19.5	54		
	switched off, V _{DD} from 1.65		T _A = 125 °C	31.5	130		
	to 3.6 V		$T_A = -40 \text{ to } 25^{\circ}\text{C}$	20	25		
			T _A = 55 °C	23	50		
			MSI clock= 131 kHz, f _{HCLK} = 131 kHz	T _A = 85 °C	25.5	55	- μΑ
	Supply			T _A = 105 °C	29.5	64	
I _{DD}	current in			T _A = 125 °C	40	140	
(LP Run)	Low-power run mode		MSI clock= 65 kHz, f _{HCLK} = 32 kHz	$T_A = -40 \text{ to } 25^{\circ}\text{C}$	22	28	
	Turi mode			T _A = 85 °C	26	68	
				T _A = 105 °C	31	75	
				T _A = 125 °C	44	95	
		All peripherals		$T_A = -40 \text{ to } 25^{\circ}\text{C}$	27.5	33	
		OFF, code	MSI clock = 65 kHz,	T _A = 85 °C	31.5	73	
		executed from Flash, V _{DD}	f _{HCLK} = 65 kHz	T _A = 105 °C	36.5	80	1
		from 1.65 V to		T _A = 125 °C	49	100	
		3.6 V		$T_A = -40 \text{ to } 25^{\circ}\text{C}$	39	46	
			MSI clock =	T _A = 55 °C	41	80	
			131 kHz,	T _A = 85 °C	44	86	
			f _{HCLK} = 131 kHz	T _A = 105 °C	49.5	100	
				T _A = 125 °C	60	120	

Table 34. Current consumption in Low-power run mode

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.



On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked OFF
 - with only one peripheral clocked on

Table 39. Peripheral current consumption in Run or Sleep mode⁽¹⁾

Peripheral		Typical	consumption, V		25 °C	
		Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	Low-power sleep and run	Unit
	CRS	2.5	2	2	2	
	DAC1	4	3.5	3	2.5	
	I2C1	11	9.5	7.5	9	
	I2C2	4	3.5	3	2.5	
	LPTIM1	10	8.5	6.5	8	
APB1	LPUART1	8	6.5	5.5	6	µA/MHz
AFDI	SPI2	9	4.5	3.5	4	(f _{HCLK})
	USB	8.5	4.5	4	4.5	
	USART2	14.5	12	9.5	11	
	TIM2	10.5	8.5	7	9	
	TIM6	3.5	3	2.5	2	
	WWDG	3	2	2	2	
	ADC1 ⁽²⁾	5.5	5	3.5	4	
	SPI1	4	3	3	2.5	
	USART1	14.5	11.5	9.5	12	
APB2	TIM21	7.5	6	5	5.5	µA/MHz
AFBZ	TIM22	7	6	5	6	(f _{HCLK})
	FIREWALL	1.5	1	1	0.5	
	DBGMCU	1.5	1	1	0.5	
	SYSCFG	2.5	2	2	1.5	

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 26* and *Table 61*, respectively.

Unless otherwise specified, the parameters given in *Table 61* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 25*.

OSPEEDRx[1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max ⁽²⁾	Unit	
	f	Maximum frequency ⁽³⁾	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz	
00	f _{max(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	- 100 K			
00	t _{f(IO)out}	Output rise and fall time	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns	
	t _{r(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	320	115	
	f	Maximum frequency ⁽³⁾	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz	
01	f _{max(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	0.6		
01	t _{f(IO)out}	Output rise and fall time	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30	ns	
	t _{r(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	65	115	
	E	Maximum frequency ⁽³⁾	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz	
10	F _{max(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2		
10	t _{f(IO)out}	Output rise and fall time	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	13	- ns	
	t _{r(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	28		
	E	Maximum frequency ⁽³⁾	C_{L} = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	35	MHz	
11	F _{max(IO)out}		C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	10		
	t _{f(IO)out}	Output rise and fall time	C_{L} = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	6		
	t _{r(IO)out}	Output rise and fall time	C_{L} = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	17	ns	
	f _{max(IO)out}	Maximum frequency ⁽³⁾		-	1	MHz	
	t _{f(IO)out}	Output fall time	C_{L} = 50 pF, V_{DD} = 2.5 V to 3.6 V	-	10		
Fm+	t _{r(IO)out}	Output rise time		-	30	ns	
configuration ⁽⁴⁾	f _{max(IO)out}	Maximum frequency ⁽³⁾		-	350	KHz	
	t _{f(IO)out}	Output fall time	C _L = 50 pF, V _{DD} = 1.65 V to 3.6 V	-	15		
	t _{r(IO)out}	Output rise time	1	-	60	ns	
-	t _{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns	

Table 61. I/O AC characteristics⁽¹⁾

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.

2. Guaranteed by design.

3. The maximum frequency is defined in *Figure 26*.

4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the line reference manual for a detailed description of Fm+ I/O configuration.



STM32L052x6 STM32L052x8

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{ADC} ⁽³⁾⁽⁴⁾	Sampling switch resistance	-	-	-	1	kΩ
C _{ADC} ⁽³⁾	Internal sample and hold capacitor	-	-	-	8	pF
↓ (3)(5)	Calibration time	f _{ADC} = 16 MHz		5.2		μs
t _{CAL} ⁽³⁾⁽⁵⁾		-		83		1/f _{ADC}
		ADC clock = HSI16	1.5 ADC cycles + 2 f _{PCLK} cycles	-	1.5 ADC cycles + 3 f _{PCLK} cycles	-
W _{LATENCY} ⁽⁶⁾	ADC_DR register write latency	ADC clock = PCLK/2	-	4.5	-	f _{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f _{PCLK} cycle
		$f_{ADC} = f_{PCLK}/2 = 16 \text{ MHz}$		μs		
		$f_{ADC} = f_{PCLK}/2$	8.5			1/f _{PCLK}
t _{latr} (3)	Trigger conversion latency	f _{ADC} = f _{PCLK} /4 = 8 MHz	0.516			μs
		f _{ADC} = f _{PCLK} /4	16.5			1/f _{PCLK}
		f _{ADC} = f _{HSI16} = 16 MHz	0.252	-	0.260	μs
Jitter _{ADC}	ADC jitter on trigger conversion	f _{ADC} = f _{HSI16}	-	1	-	1/f _{HSI16}
ts ⁽³⁾	Compling time	f _{ADC} = 16 MHz	0.093	-	10.03	μs
ts ^(e)	Sampling time	-	1.5	-	160.5	1/f _{ADC}
t _{UP_LDO} ⁽³⁾⁽⁵⁾	Internal LDO power-up time	-	-	-	10	μs
t _{STAB} ⁽³⁾⁽⁵⁾	ADC stabilization time	-	14		1/f _{ADC}	
+ (3)	Total conversion time	f _{ADC} = 16 MHz, 12-bit resolution	0.875	-	10.81	μs
t _{ConV} ⁽³⁾	(including sampling time)	12-bit resolution	14 to 173 (t _S for sampling +12.5 for successive approximation)		1/f _{ADC}	

Table 63. ADC characteristics (continued)

1. V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to Table 64: RAIN max for fADC = 16 MHz.

2. A current consumption proportional to the APB clock frequency has to be added (see *Table 39: Peripheral current consumption in Run or Sleep mode*).

3. Guaranteed by design.

 Standard channels have an extra protection resistance which depends on supply voltage. Refer to Table 64: RAIN max for fADC = 16 MHz.

5. This parameter only includes the ADC timing. It does not take into account register access latency.

6. This parameter specifies the latency to transfer the conversion result into the ADC_DR register. EOC bit is set to indicate the conversion is complete and has the same latency.



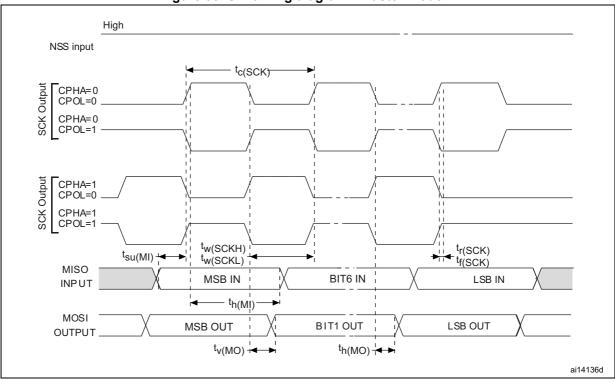


Figure 35. SPI timing diagram - master mode⁽¹⁾

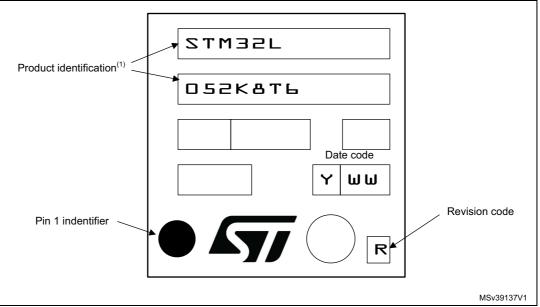
1. Measurement points are done at CMOS levels: $0.3V_{\text{DD}}$ and $0.7V_{\text{DD}}$

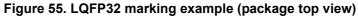


Device marking for LQFP32

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.





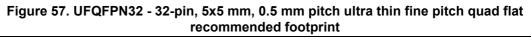
 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

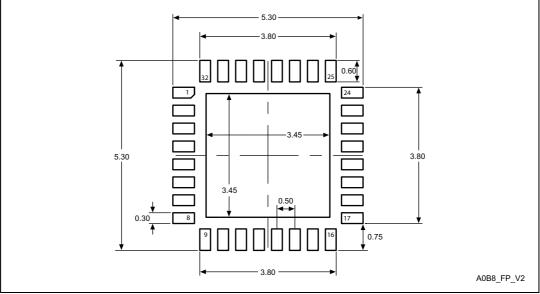


	package mechanical data								
Symbol	millimeters			inches ⁽¹⁾					
	Min	Тур	Max	Min	Тур	Мах			
А	0.500	0.550	0.600	0.0197	0.0217	0.0236			
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020			
A3	-	0.152	-	-	0.0060	-			
b	0.180	0.230	0.280	0.0071	0.0091	0.0110			
D	4.900	5.000	5.100	0.1929	0.1969	0.2008			
D1	3.400	3.500	3.600	0.1339	0.1378	0.1417			
D2	3.400	3.500	3.600	0.1339	0.1378	0.1417			
E	4.900	5.000	5.100	0.1929	0.1969	0.2008			
E1	3.400	3.500	3.600	0.1339	0.1378	0.1417			
E2	3.400	3.500	3.600	0.1339	0.1378	0.1417			
е	-	0.500	-	-	0.0197	-			
L	0.300	0.400	0.500	0.0118	0.0157	0.0197			
ddd	-	-	0.080	-	-	0.0031			

Table 90. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flatpackage mechanical data

1. Values in inches are converted from mm and rounded to 4 decimal digits.





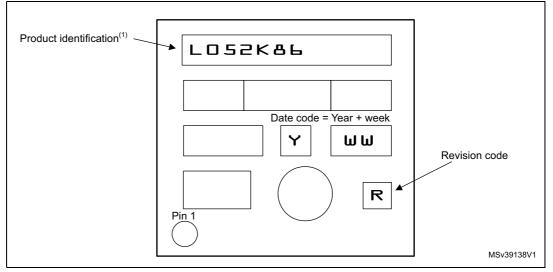
1. Dimensions are expressed in millimeters.

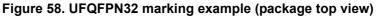


Device marking for UFQFPN32

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



9 Revision history

Date	Revision	Changes	
27-Feb-2014	1	Initial release.	
29-Apr-2014	2	Added WLCSP36 package. Updated Table 2: Ultra-low-power STM32L052x6/x8 device features and peripheral counts Updated Figure 4: STM32L052x6/8 TFBGA64 ballout - 5x 5 mm. Updated Table 5: Functionalities depending on the working mode (from Run/active down to standby). Added Section 3.2: Interconnect matrix. Replaced Ta I/O structure by TC, updated PA0/4/5, PC5/14, BOOTO and NRST I/O structure, and added note 3 in Table 16: STM32L052x6/8 pin definitions. Updated Table 25: General operating conditions, Table 22: Voltage characteristics and Table 23: Current characteristics. Modified conditions in Table 28: Embedded internal reference voltage. Updated Table 29: Current consumption in Run mode, code with data processing running from Flash, Table 31: Current consumption in Run mode, code with data processing running from RAM, Table 33: Current consumption in Sleep mode, Table 34: Current consumption in Low- power run mode, Table 35: Current consumption in Low-power sleep mode, and Table 36: Typical and maximum current consumptions in Standby mode. Added Figure 14: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS, Figure 15: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSI16, 1WS, Figure 16: IDD vs VDD, at TA= 25/55/85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, Figure 17: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 18: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF. Updated Table 46: ESD absolute maximum ratings, Table 58: I/O current injection susceptibility and Table 59: I/O static characteristics, and added Figure 24: VIH/VIL versus VDD (CMOS I/Os) and Figure 25: VIH/VIL versus VDD (TTL I/Os). Updated Table 60: Cutput voltage characteristics definition. Updated Table 56: ESD absolute maximum ratings, Table 58: I/O current injection susceptibility a	

Table 93. Document revision history



Date	Revision	Changes	
05-Sep-2014	4	Extended operating temperature range to 125 °C. Updated minimum ADC operating voltage to 1.65 V. Changed number of I2S interface from 1 to 0 in <i>Table 2: Ultra-low- power STM32L052x6/x8 device features and peripheral counts</i> . Replaced USART3 by LPUART1 in <i>Table 16: STM32L052x6/8 pin</i> <i>definitions</i> and LPUART by LPUART1 in <i>Table 17: Alternate function</i> <i>port A, Table 18: Alternate function port B, Table 19: Alternate function</i> <i>port C, Table 20: Alternate function port D</i> and <i>Table 21: Alternate</i> <i>function port H</i> . Updated PA6 in <i>Table 17: Alternate function port A</i> . Updated temperature range in <i>Section 1: Description</i> , <i>Table 2: Ultra- low-power STM32L052x6/x8 device features and peripheral counts</i> . Updated PD, <i>T_{A and} T_J</i> to add range 3 in <i>Table 25: General operating</i> <i>conditions</i> . Added range 3 in <i>Table 53: Flash memory</i> and data <i>EEPROM</i> endurance and retention, <i>Table 92: STM32L052x6/8</i> <i>ordering information scheme</i> . Update note 1 in <i>Table 29: Current</i> <i>consumption in Run mode, code with data processing running from</i> <i>Flash</i> , <i>Table 31: Current consumption in Rum mode, code with data</i> <i>processing running from RAM</i> , <i>Table 33: Current consumption in Sleep</i> <i>mode</i> , <i>Table 34: Current consumptions in Stop mode</i> , <i>Table 37:</i> <i>Typical and maximum current consumptions in Stop mode, Table 37:</i> <i>Typical and maximum current consumptions in Stop mode, rable 37:</i> <i>Typical and maximum current consumptions in Stop mode, code running</i> <i>from RAM</i> , <i>Range 3</i> , <i>MSI (Range 0) at 64 KHz, 0 WS</i> , <i>Figure 17: IDD</i> vs <i>VDD</i> , at <i>TA= 25/55/ 85/105/125 °C</i> , <i>Stop mode with RTC enabled</i> <i>and running on LSE Low drive, Figure 18: IDD</i> vs <i>VDD</i> , at <i>TA=</i> <i>25/55/85/105/125 °C</i> , <i>Stop mode with RTC disabled, all clocks OFF</i> . Updated <i>Table 43: Low-speed external user clock characteristics</i> . Updated <i>Table 43: Low-speed external user clock characteristics</i> . Updated <i>ACC</i> _{HSI16} temperature conditions in <i>Table 46: 16 MHz HSI16</i> <i>oscillator characteristics</i> . Changed ambient temperature range in notet	

Table 93. Document revision history (continued)

